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Kind regards,

Team Nexperia



PMBTA42 300 V, 100 mA NPN high-voltage transistor Rev. 05 – 12 December 2008

Product data sheet

1. Product profile

1.1 General description

NPN high-voltage transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: PMBTA92.

1.2 Features

High voltage (max. 300 V)

1.3 Applications

Telephony and professional communication equipment

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	300	V
I _C	collector current		-	-	100	mA
h _{FE}	DC current gain	V _{CE} = 10 V				
		$I_{\rm C} = 1 \rm{mA}$	25	-	-	
		I _C = 10 mA	40	-	-	
		I _C = 30 mA	40	-	-	

2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter		3
3	collector		



300 V, 100 mA NPN high-voltage transistor

3. Ordering information

Type number ^[1]	Package		
	Name	Description	Version
PMBTA42	-	plastic surface-mounted package; 3 leads	SOT23
PMBTA42/DG			

4. Marking

Type number ^[1]	Marking code ^[2]	
PMBTA42	*1D	
PMBTA42/DG	*BV	

- [2] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	300	V
V _{CEO}	collector-emitter voltage	open base	-	300	V
V _{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current		-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	200	mA
I _{BM}	peak base current	single pulse; $t_p \leq 1 \text{ ms}$	-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

300 V, 100 mA NPN high-voltage transistor

6. Thermal characteristics

Table 7.

Characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1] -	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = 200 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 6 V; I_C = 0 A$	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V				
		$I_{\rm C} = 1 \rm{mA}$	25	-	-	
		I _C = 10 mA	40	-	-	
		I _C = 30 mA	40	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C}$ = 20 mA; $I_{\rm B}$ = 2 mA	-	-	500	mV
V _{BEsat}	base-emitter saturation voltage	$I_{\rm C}$ = 20 mA; $I_{\rm B}$ = 2 mA	-	-	900	mV
C _{re}	feedback capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB} = 20 \ V; \ I_{C} = i_{c} = 0 \ A; \\ f = 1 \ MHz \end{array}$	-	-	3	pF
f _T	transition frequency	V _{CE} = 20 V; I _C = 10 mA; f = 100 MHz	50	-	-	MHz

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8. Package outline

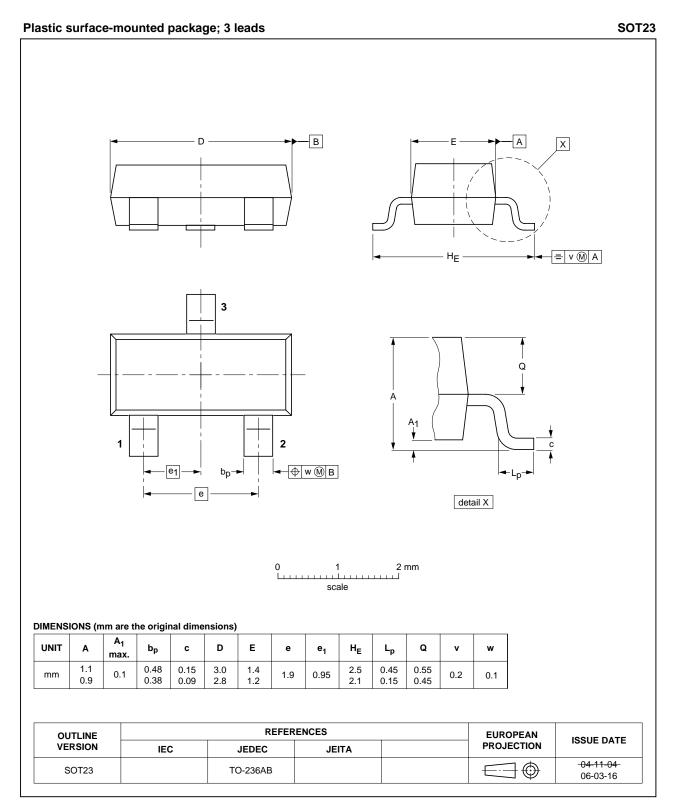


Fig 1. Package outline SOT23 (TO-236AB)

300 V, 100 mA NPN high-voltage transistor

9. Packing information

Table 8. Packing methods

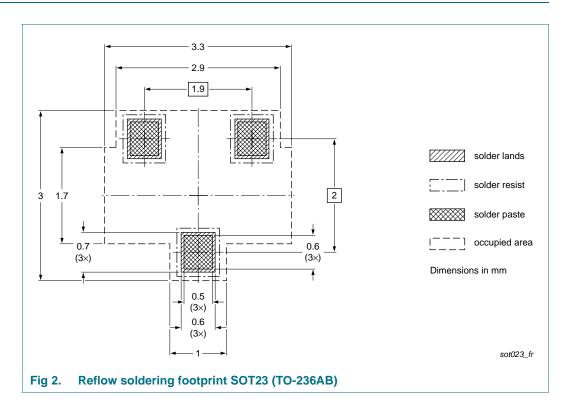
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Package Description		Packing quantity		
				3000	10000	
PMBTA42	SOT23	4 mm pitch, 8 mm tape and reel		-215	-235	
PMBTA42/DG						

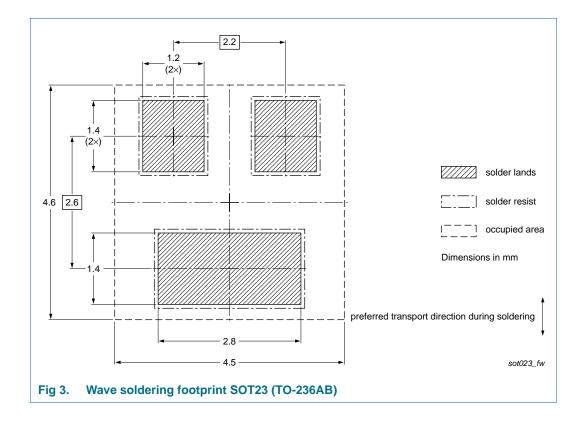
[1] For further information and the availability of packing methods, see <u>Section 13</u>.

[2] /DG: halogen-free

10. Soldering



300 V, 100 mA NPN high-voltage transistor



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11. Revision history

Table 9. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBTA42_5	20081212	Product data sheet	-	PMBTA42_4
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity
	 Legal texts 	have been adapted to the n	ew company name whe	ere appropriate.
	 Type numb 	er PMBTA42/DG added		
	Table 4 "Ma	urking codes": enhanced		
	Section 12	"Legal information": updated	t	
PMBTA42_4	20040122	Product specification	-	PMBTA42_3
PMBTA42 3	19990422	Product specification	-	PMBTA42 43 CNV 2

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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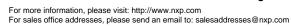
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